

METHOD FOR IMPROVED PLASMA NITRIDATION OF ULTRA THIN GATE DIELECTRICS

ABSTRACT

5 A method for forming a gate dielectric for an integrated circuit device. In an exemplary embodiment of the invention, the method includes forming an initial oxynitride layer upon a substrate material, the oxynitride layer having an initial physical thickness. The initial oxynitride layer is then subjected to a plasma nitridation, the plasma nitridation resulting in final oxynitride layer having a final physical thickness.